

Supplementary Information

Complete Surface Coverage of ZnO Nanorod Arrays by Pulsed electrodeposited CuInS₂ for Visible Light Energy Conversion

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Experimental details

Preparation of a ZnO nanorod film on a FTO substrate

A ZnO nanorod film was prepared by a chemical bath deposition (CBD) method. A seeding
technique was used prior to CBD process, involving the formation of ZnO seed particles on the
15 cleaned FTO substrate by the thermal decomposition of zinc acetate. [1] The FTO substrates were
pre-cleaned with Milli-Q water, ethanol (99.5%, Sigma-Aldrich) and acetone (99.8%, Chem-
Supply) under mild sonication followed by drying in vacuum before use. Several drops of a
solution containing 0.005 mol/L of zinc acetate (Ajax Finechem) dissolved in ethanol were
20 applied on the transparent FTO substrates. After 10 seconds, the substrate was rinsed with ethanol
and dried with nitrogen gas. The dropwise process with zinc acetate was repeated for five times
before calcined for 20 min at 350 °C to form ZnO seeds from thermal decomposition of zinc
acetate. The whole seeding procedure was repeated for two times to obtain an evenly distributed
ZnO seed layer on the FTO substrate.

After that, the seeded substrate was sealed in a scotch bottle with 100 mL aqueous solution
25 consisted of half 0.05 mol/L of zinc nitrate (98%, Sigma-Aldrich) and half 0.05 mol/L of
hexamethylenetetramine (99%, Sigma-Aldrich), commonly used as a structure-directing agent.[2]
Each solution was preheated to 90°C for 5 min before mixing together to speed up the reaction in
the CBD process. The bottle was then kept in the oven at 90°C for 3 h for the first growth cycle.
The second cycle was done by simply topping up fresh solutions and repeating the first cycle. The
30 obtained ZnO nanorod thin films were rinsed thoroughly in Milli-Q water and dried in air. At last,
the transparent ZnO nanorod film was calcined for 30 min at 450 °C to completely remove the
remaining organic components.

Preparation of CuInS₂ nanoparticles on the ZnO nanorod film

CuInS₂ nanoparticles on the ZnO nanorod film were deposited by a pulsed electrodeposition
35 method, the resultant ZnO/FTO film as the working electrode and a Pt foil as the counter
electrode. The CuInS₂ nanoparticles was deposited electrochemically by applying a repetitive on-

off time square pulse generated by a functional generator (TG4001, Thurlby Thandar Instruments), applying a cathodic pulse (-1.25 V, 100 ms) and short-circuit pulse (0 V, 100 ms) alternatively. Depending on the electrolyte chosen, two pulsed electrodeposition methods, namely simultaneously pulsed electrodeposition and sequential pulsed-electrodeposition, were chosen to deposit CuInS₂ on ZnO nanorods. The details of the precursors as well as the sample names chosen for the pulsed electrodeposition are presented in the table below. For a simultaneously pulsed electrodeposition, i.e. “simultaneous Cu and In deposition” sample, 60 mL of an aqueous solution containing 10 mmol/L of CuCl₂ (99.9%, Ajax Finechem), 10 mmol/L of InCl₃ (98%, Sigma-Aldrich) and 100 mmol/L of Na₂S₂O₃ (98%, Sigma-Aldrich) was chosen for the electrolyte in the two-electrode cell. Similarly, for a sequential pulsed-electrodeposition, the same concentrations of Cu/In/S precursors were deposited in two steps, namely (1) “Cu deposition followed by In” and (2) “In deposition followed by Cu” samples.

Table S1: Experimental sequences for CuInS₂-ZnO obtained from simultaneous and sequential pulsed-electrodeposition.

Method Name	Sample Name	Precursors for Pulsed Electrodeposition	
Simultaneously PED	“simultaneous Cu and In deposition”	Step 1: CuCl ₂ , InCl ₃ , Na ₂ S ₂ O ₃	
Sequential I PED	“Cu deposition followed by In”	Step 1: CuCl ₂ , Na ₂ S ₂ O ₃	Step 2: InCl ₃
Sequential II PED	“In deposition followed by Cu”	Step 1: InCl ₃ , Na ₂ S ₂ O ₃	Step 2: CuCl ₂

The-obtained CuInS₂/ZnO film was dried and annealed at 500 °C for 1 h in a gas mixture of 92% N₂ and 8% H₂ to facilitate crystallization. Before the heating, N₂ was purged through the tube furnace for 2 h to completely remove the air. Subsequently, the heating was performed with the ramping rate of 5 °C/min from room temperature to 500°C. The gas flow rate was maintained at 50 mL/min throughout the process.

Characterization of the obtained CuInS₂-ZnO films

The crystallographic phase structures of the deposited films were characterized using an X-ray diffractometer (X’pert Pro MRD, Philips) with Cu K_α radiation at 45 kV and 40 mA, a step size of 0.013° and a scan step time at 97.92 s in the 2θ range of 25° to 60°. The morphological features were determined using a scanning electron microscope (SEM, S900 Hitachi). The UV-Vis diffuse reflectance spectra were obtained using a UV/Vis/NIR spectrophotometer (Perkin Elmer LAMBDA 1050) with GaP (1200-900nm) and Si (900-250nm) detectors. A high-resolution transmission electron microscopy (HRTEM, CM200 Philips) was employed to examine the lattice fringes of electrodeposited CuInS₂ and ZnO crystals, as well as the interface between the CuInS₂ nanoparticles and the ZnO nanorod film. The CuInS₂ film thickness can be estimated from the TEM image of an individual ZnO nanorod after coating (Figure S4). Elemental mapping of the resultant CuInS₂-ZnO was performed using SEM-EDAX. See Figure S5 for the results.

Photoelectrochemical (PEC) characterization

The photoelectrochemical properties of the CuInS₂-ZnO films were examined under potentiostatic conditions in a three-electrode system using CuInS₂-ZnO films as the working electrode, Ag/AgCl as the reference electrode and a platinum wire as the counter electrode in an aqueous solution containing 0.25 mol/L of Na₂S and 0.35 mol/L of Na₂SO₃ at pH 12. An electrolytic cell made out of Teflon with a flat quartz window was used. The photocurrent responses were measured under visible light illumination using a 300 W Xenon lamp with a cut off filter ($\lambda \geq 435$ nm). The illuminated area of the working electrode was fixed at 0.196 cm².

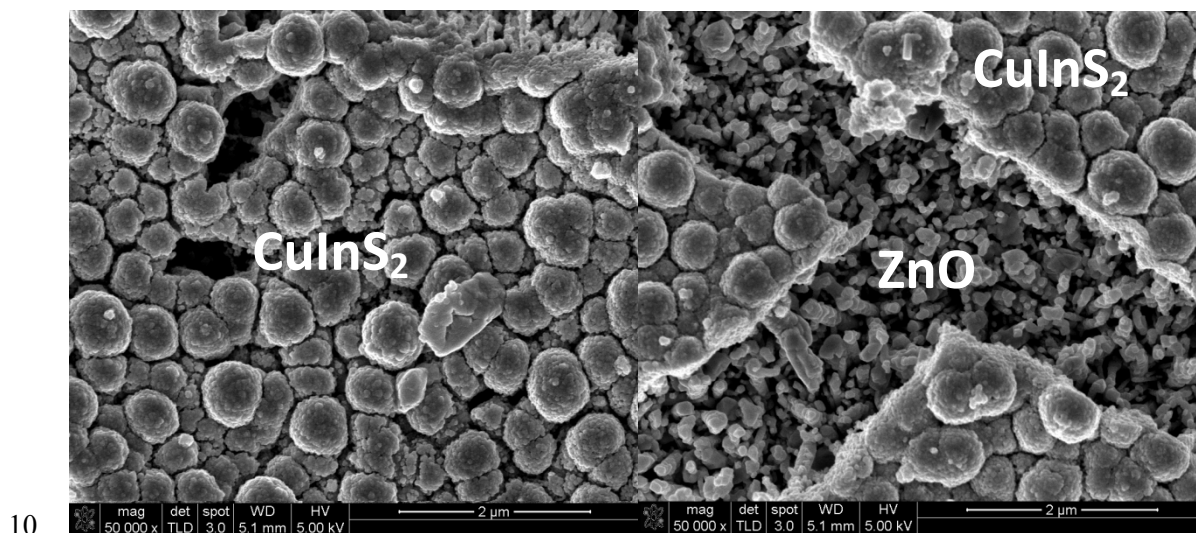


Figure S1 Surface morphology of CuInS₂-ZnO from non-pulsed electrodeposition for 10 min using Cu/In/S precursors in the electrolyte

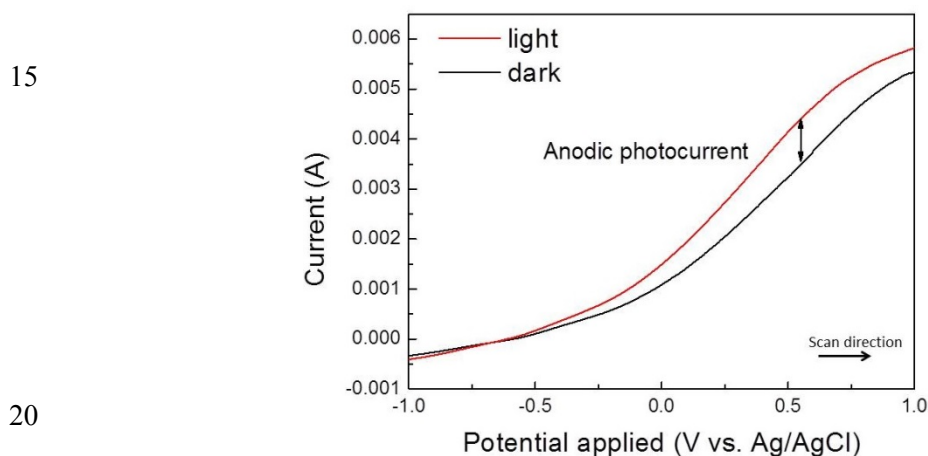


Figure S2 Current-voltage curve of CuInS₂ (reference electrode: Ag/AgCl)

The CuInS₂ prepared in this work is an n-type semiconductor. The n-type behavior of CuInS₂ is indicated by the current-voltage measurement in Figure S2. The anodic photocurrent generated upon visible light (> 435 nm) verified its n-type nature.

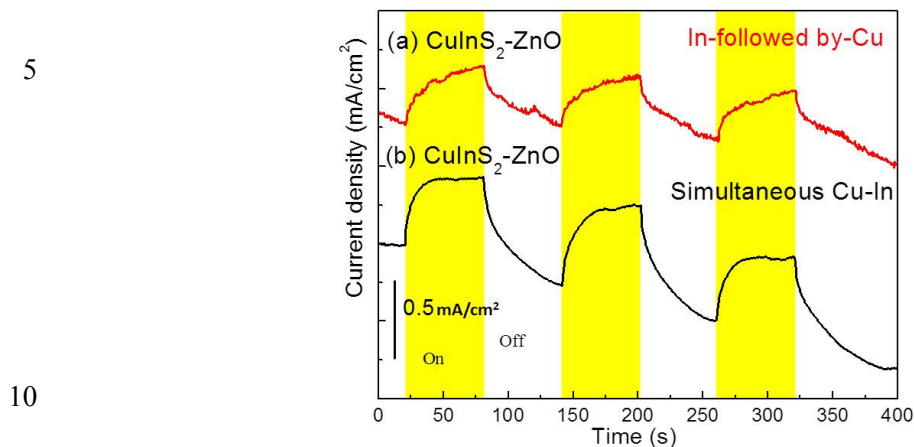


Figure S3 Photocurrent response of pulsed electrodeposited CuInS₂-ZnO under different conditions at 0.75 V vs. Ag/AgCl in electrolyte containing 0.25 mol/L Na₂S and 0.35 mol/L Na₂SO₃ (pH = 12) under visible light irradiation ($\lambda \geq 435$ nm)

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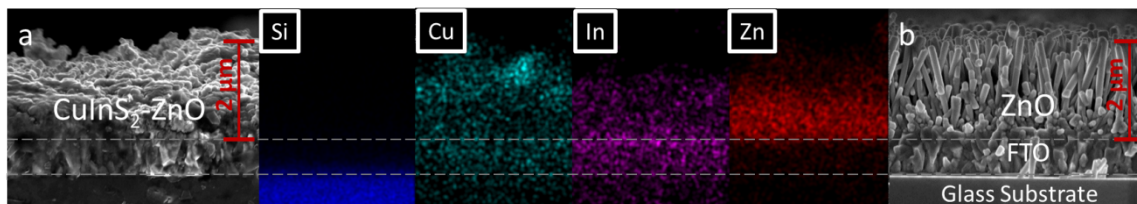


Figure S4 (a) Cross-sectional SEM image and SEM-EDX mapping of CuInS₂-ZnO using “Cu deposition followed by In” method (b) Cross-sectional SEM image of bare ZnO

Film thicknesses of ZnO and CuInS₂-ZnO films were estimated from the cross-sectional SEM images as shown below. The bare ZnO nanorods film has the thickness of ~2 μm while the CuInS₂-ZnO composite is thinner at ~1.3 μm on average. The complementary EDAX elemental mapping of CuInS₂-ZnO film supports the identification of the individual component in the composite film. The thinner CuInS₂-ZnO layer was also evident by the lower XRD peak intensity for ZnO (Figure 1, manuscript) as compared with the bare ZnO film. The shortened ZnO is attributed to its chemical dissolution promoted by the H⁺ released from the metallic precursors. This is confirmed by the detection of dissolved Zn in the electrolyte after the electrodeposition using ICP analysis.

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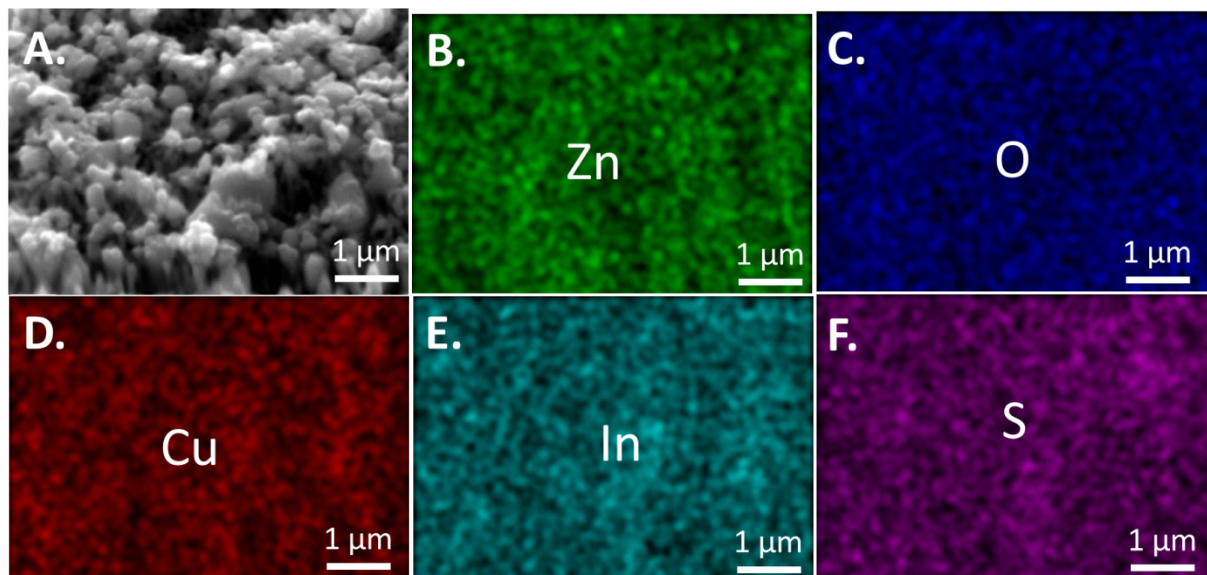


Figure S5 SEM-EDAX mapping of CuInS₂-ZnO film

The elemental mapping of the tilted top view over a considerable area of CuInS₂-ZnO confirms the presence of elemental Cu, In, S, Zn and O. Good homogeneity of the electrodeposition is achieved. Combined with the HRTEM image analyzing the interface, ZnO nanorods have been successfully deposited with CuInS₂.

References

- 10 [1] L. Vayssieres, *Adv. mater.*, 2003, **15**, 464.
 [2] L. Vayssieres, K. Keis, S.-E. Lindquist and A. Hagfeldt, *J. Phys. Chem. B*, 2001, **105**, 3350 .